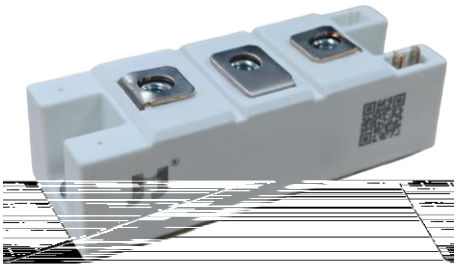
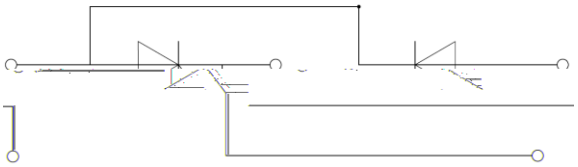
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FIG.1: Power dissipation vs. on-state current (per thyristor or diode)

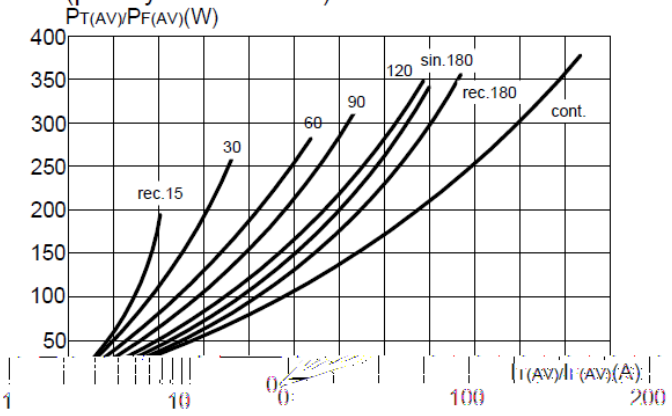


FIG.2: Maximum transient thermal impedance junction to case(per thyristor or diode)

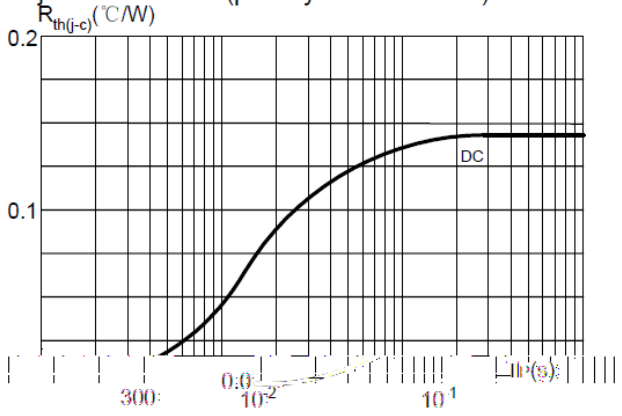


FIG.3: Forward characteristics (per thyristor or diode)

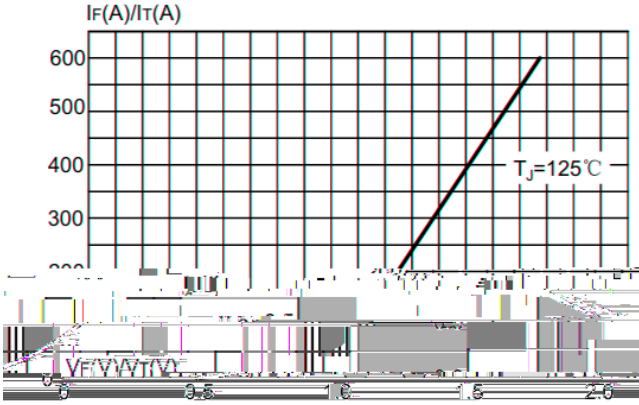


FIG.4: Relative variation of gate trigger current, holding current and latching current versus junction temperature

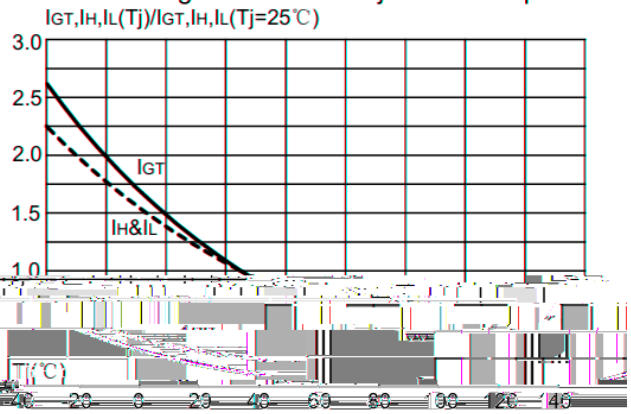


FIG.5 Gate trigger characteristics

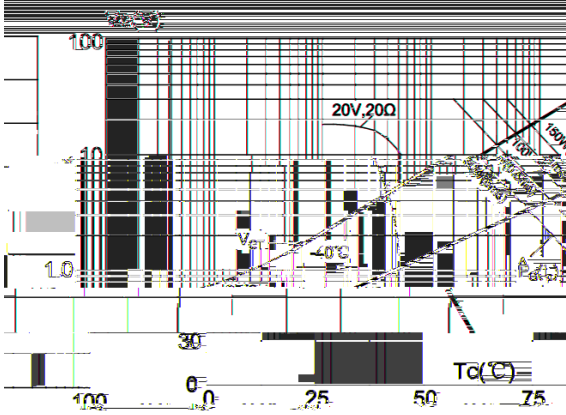


FIG.6: Forward current vs. case temperature

